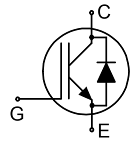
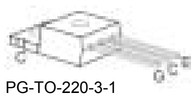
Low Loss DuoPack : IGBT in TrenchStop® and Fieldstop technology with soft, fast recovery anti-parallel EmCon HE diode



- Very low $V_{CE(sat)}$ 1.5 V (typ.)
- Maximum Junction Temperature 175 °C
- Short circuit withstand time – 5µs
- Designed for :
  - Variable Speed Drive for washing machines, air conditioners and induction cooking
  - Uninterrupted Power Supply
- TrenchStop® and Fieldstop technology for 600 V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Very soft, fast recovery anti-parallel EmCon HE diode
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/


PG-TO-220-3-1

Type	V_{CE}	I_C	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking Code	Package
IKP10N60T	600V	10A	1.5V	175°C	K10T60	PG-TO-220-3-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{jmax} T_C = 25°C T_C = 100°C	I_C	 20 10	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	30	
Turn off safe operating area $V_{CE} \leq$ 600V, $T_j \leq$ 175°C	-	30	
Diode forward current, limited by T_{jmax} T_C = 25°C T_C = 100°C	I_F	 20 10	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	30	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)] V_{GE} = 15V, $V_{CC} \leq$ 400V, $T_j \leq$ 150°C	t_{SC}	5	µs
Power dissipation T_C = 25°C	P_{tot}	110	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	
Soldering temperature, wavesoldering, 1.6 mm (0.063 in.) from case for 10s		260	

[1] J-STD-020 and JESD-022
[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		1.35	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.9	
Thermal resistance, junction – ambient	R_{thJA}		62	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=0.2mA	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=10A T_j=25°C T_j=175°C	 - -	 1.5 1.8	 2.05 -	
Diode forward voltage	V_F	V_{GE}=0V, I_F=10A T_j=25°C T_j=175°C	 - -	 1.6 1.6	 2.0 -	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=0.3mA, V_{CE}=V_{GE}	4.1	4.6	5.7	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V, V_{GE}=0V T_j=25°C T_j=175°C	 - -	 - -	 40 1000	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=10A	-	6	-	S
Integrated gate resistor	R_{Gint}			none		Ω

Dynamic Characteristic

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Input capacitance	C_{iss}	V_{CE}=25V,	-	551	-	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	40	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	17	-	
Gate charge	Q_{Gate}	V_{CC}=480V, I_C=**Fehler! Verweisquelle konnte nicht gefunden werden.**A V_{GE}=15V	-	62	-	nC

Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH
Short circuit collector current[1]	$I_{C(SC)}$	V_{GE}=15V, $t_{SC}\le$5µs V_{CC} = 400V, T_j = 25°C	-	100	-	A

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=400V, I_C=10A, V_{GE}=0/15V, R_G=23Ω, L_σ[2)]=60nH, C_σ[2)]=40pF Energy losses include "tail" and diode reverse recovery.	-	12	-	ns
Rise time	t_r		-	8	-	
Turn-off delay time	$t_{d(off)}$		-	215	-	
Fall time	t_f		-	38	-	
Turn-on energy	E_{on}		-	0.16	-	mJ
Turn-off energy	E_{off}		-	0.27	-	
Total switching energy	E_{ts}		-	0.43	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=25°C, V_R=400V, I_F=10A, di_F/dt=880A/µs	-	115	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.38	-	µC
Diode peak reverse recovery current	I_{rrm}		-	10	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	680	-	A/µs

Switching Characteristic, Inductive Load, at T_j=175 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=175°C, V_{CC}=400V, I_C=10A, V_{GE}=0/15V, R_G= 23Ω, L_σ[1)]=60nH, C_σ[1)]=40pF Energy losses include "tail" and diode reverse recovery.	-	10	-	ns
Rise time	t_r		-	11	-	
Turn-off delay time	$t_{d(off)}$		-	233	-	
Fall time	t_f		-	63	-	
Turn-on energy	E_{on}		-	0.26	-	mJ
Turn-off energy	E_{off}		-	0.35	-	
Total switching energy	E_{ts}		-	0.61	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=175°C V_R=400V, I_F=10A, di_F/dt=880A/µs	-	200	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.92	-	µC
Diode peak reverse recovery current	I_{rrm}		-	13	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	390	-	A/µs

1) Allowed number of short circuits: <1000; time between short circuits: >1s.
2) Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.
1) Leakage inductance L_σ and Stray capacity C_σ due to dynamic test circuit in Figure E.

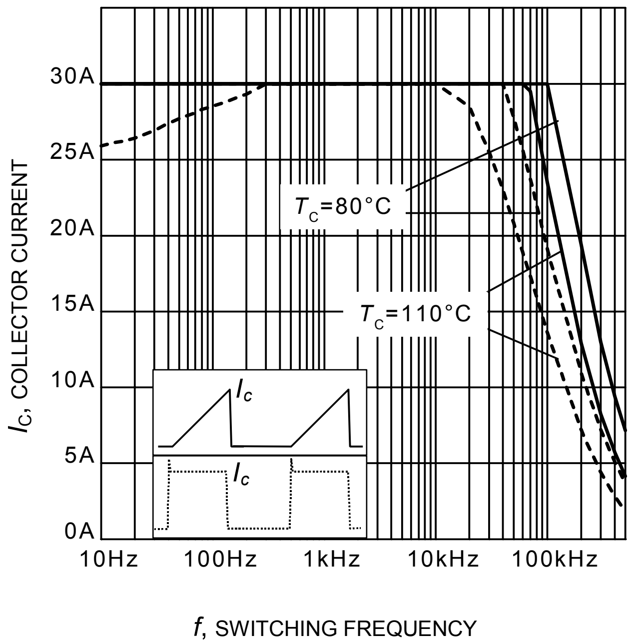


Figure 1. Collector current as a function of switching frequency
($T_j \leq 175°C$, $D = 0.5$, $V_{CE} = 400V$, $V_{GE} = 0/+15V$, $R_G = 23\Omega$)

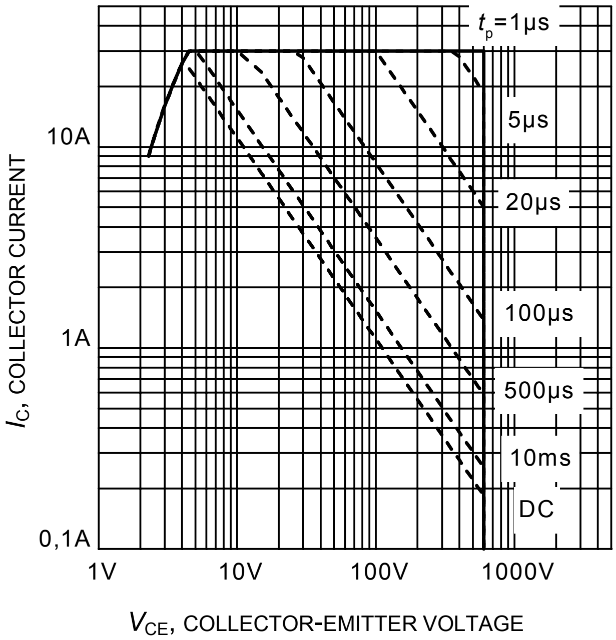


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 175°C$; V_{GE}=15V)

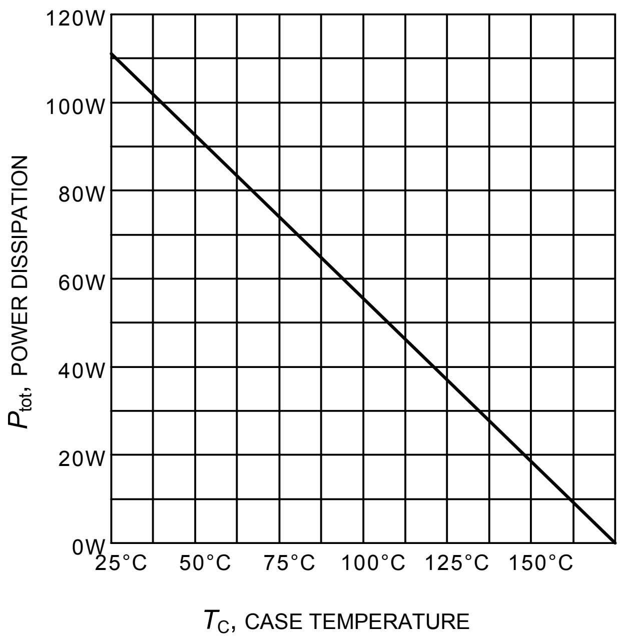


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 175°C$)

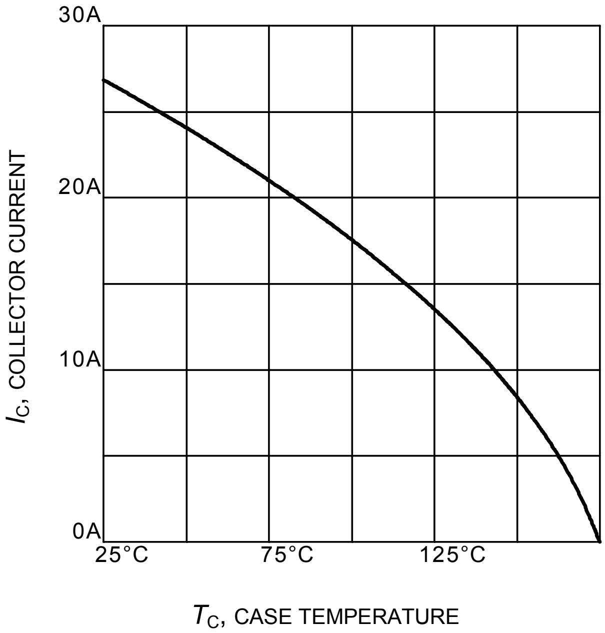


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15V$, $T_j \leq 175°C$)

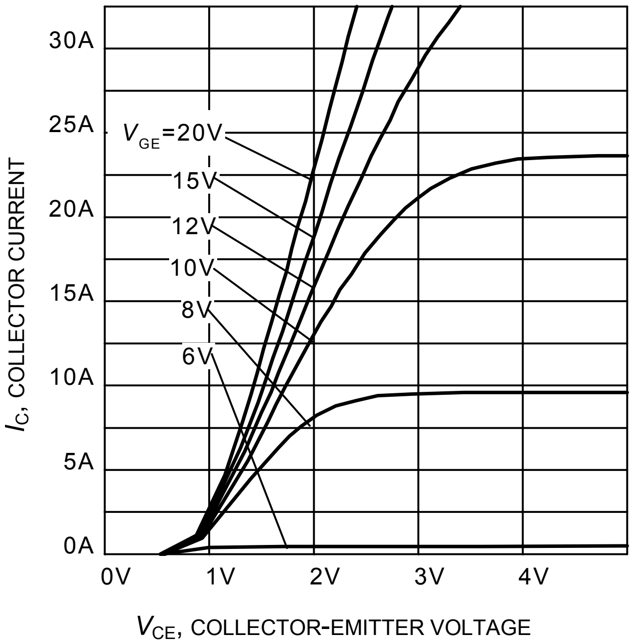


Figure 5. Typical output characteristic
(T_j = 25°C)

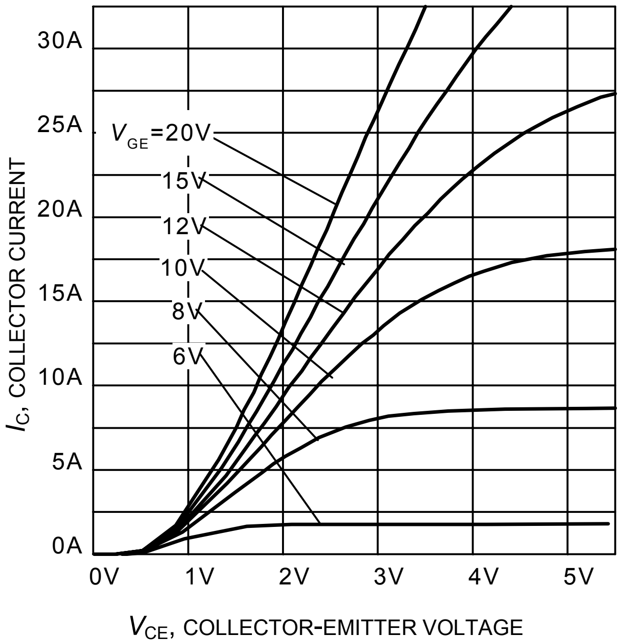


Figure 6. Typical output characteristic
(T_j = 175°C)

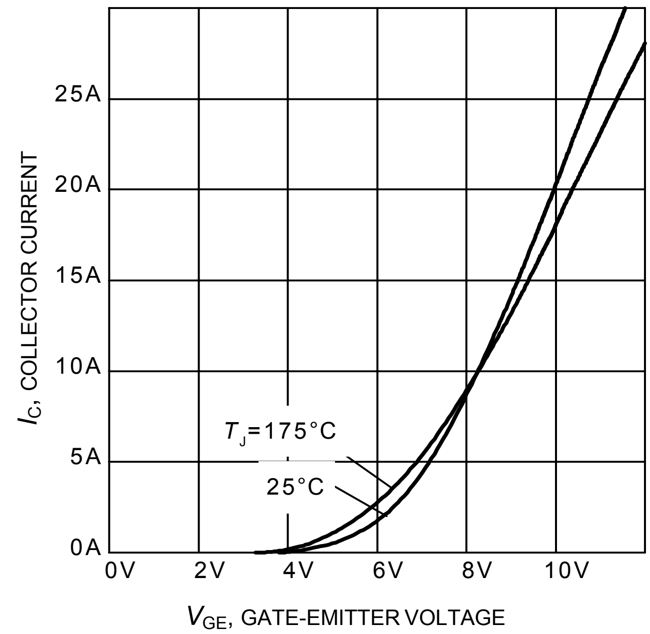


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

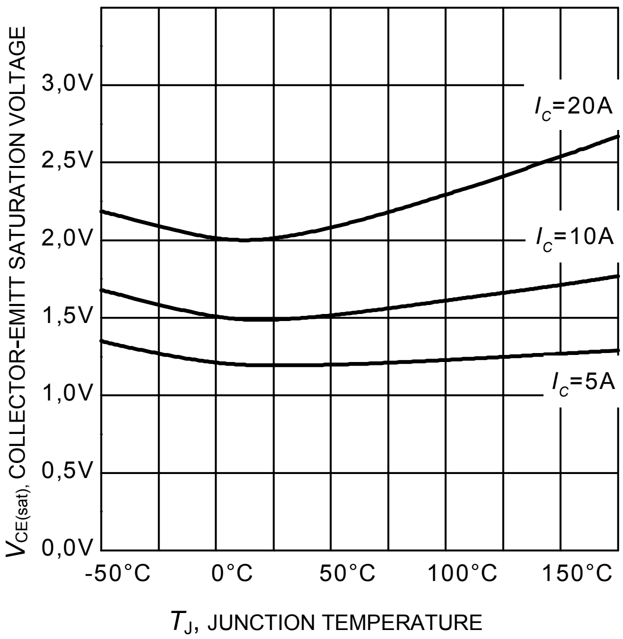


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

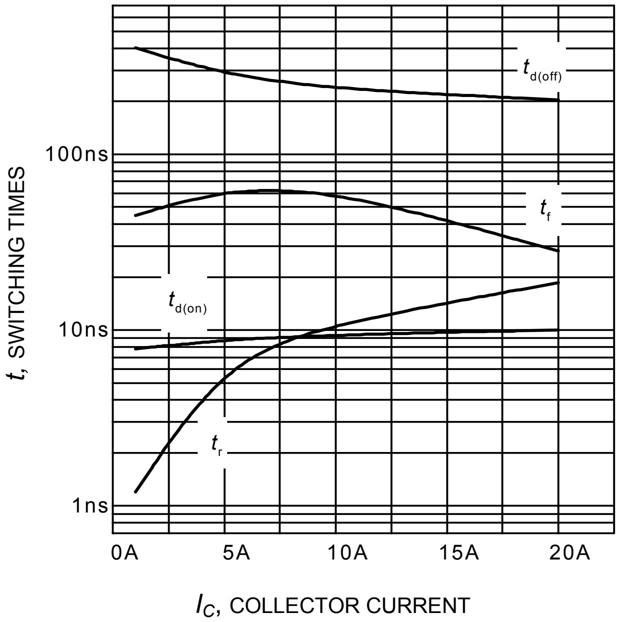


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=175°C, V_{CE} = 400V, V_{GE} = 0/15V, R_G = 23Ω, Dynamic test circuit in Figure E)

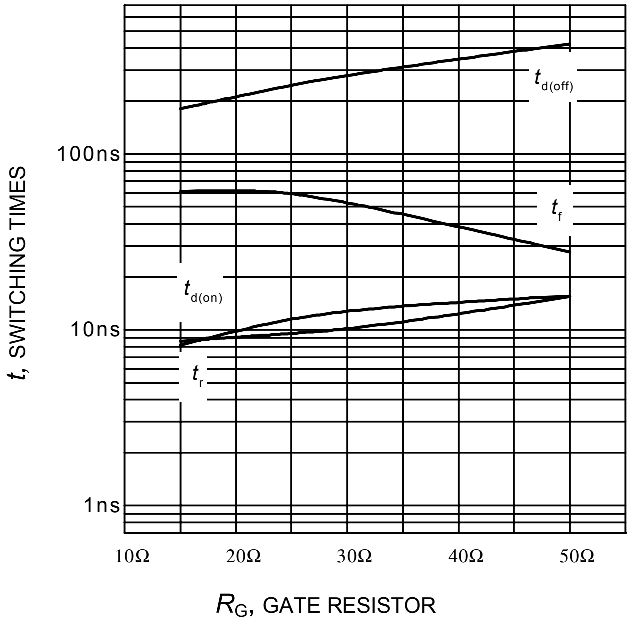


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE}= 400V, V_{GE} = 0/15V, I_C = 10A, Dynamic test circuit in Figure E)

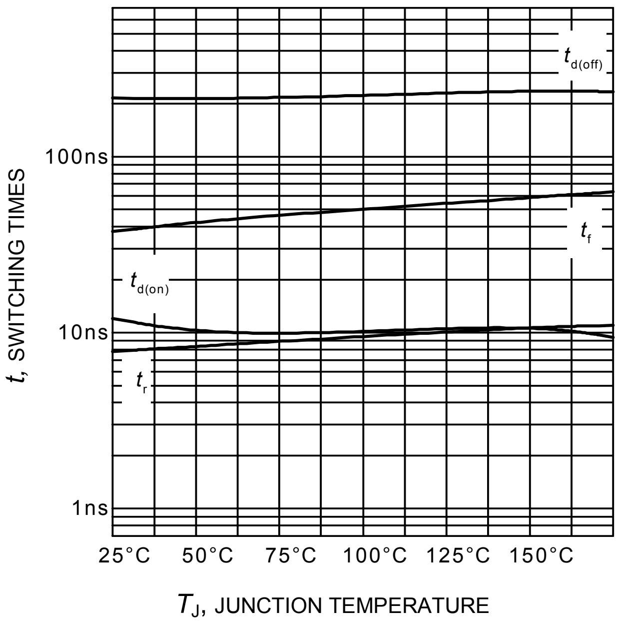


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 10A, R_G=23Ω, Dynamic test circuit in Figure E)

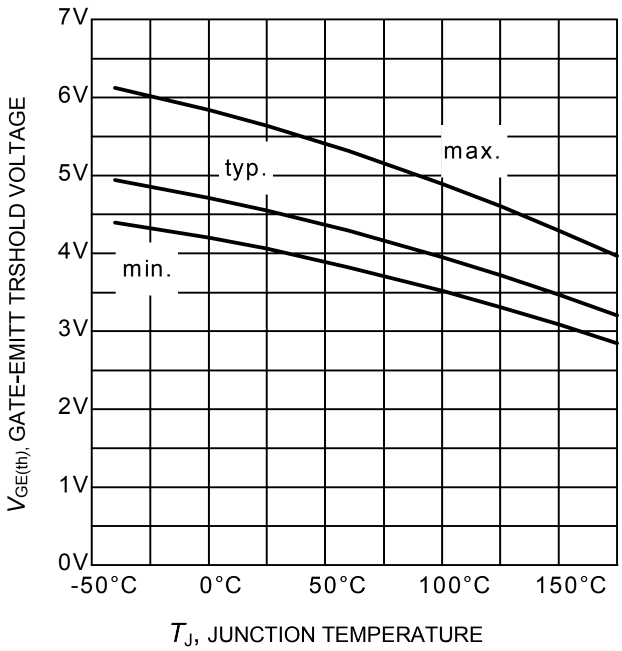


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.3mA)

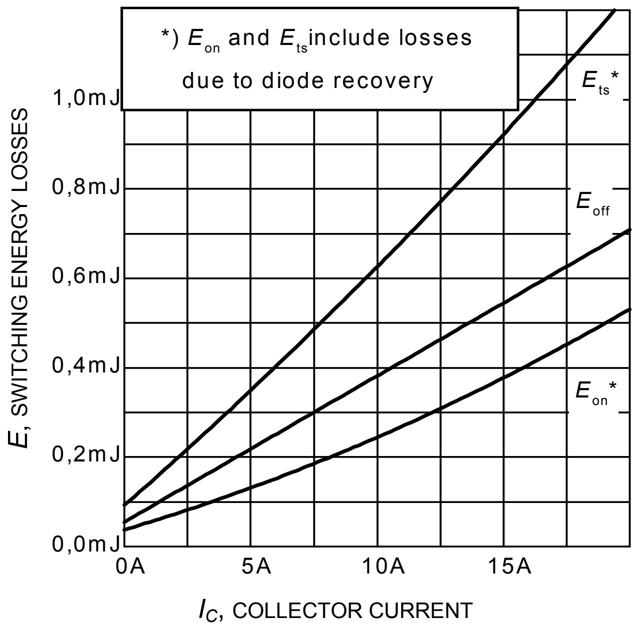


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, R_G = 23Ω, Dynamic test circuit in Figure E)

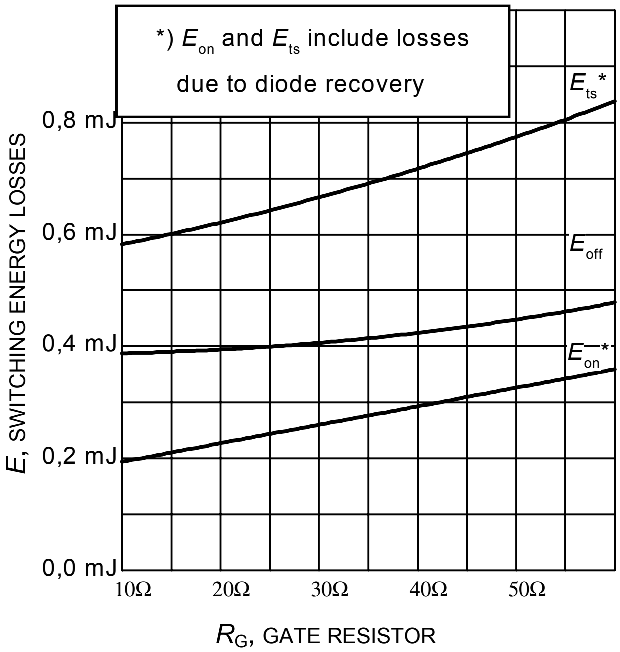


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 10A, Dynamic test circuit in Figure E)

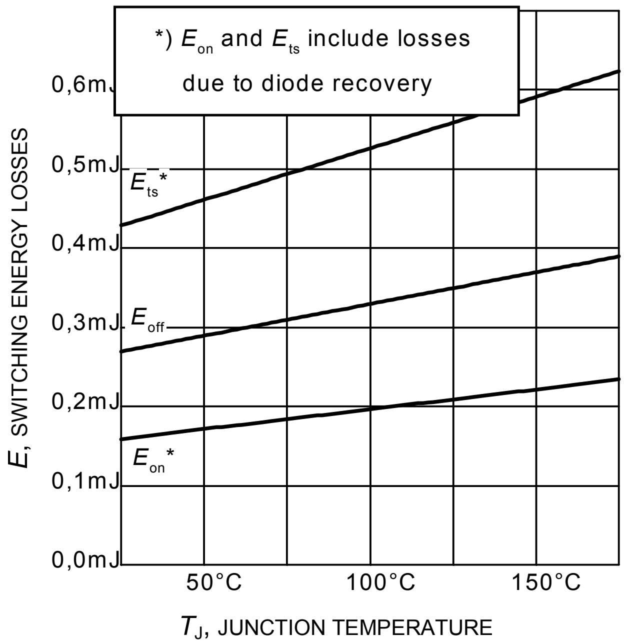


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 10A, R_G = 23Ω, Dynamic test circuit in Figure E)

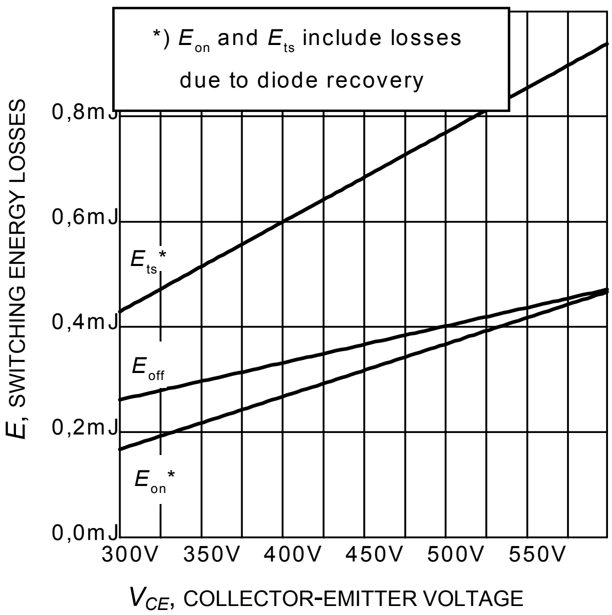


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J = 175°C, V_{GE} = 0/15V, I_C = 10A, R_G = 23Ω, Dynamic test circuit in Figure E)

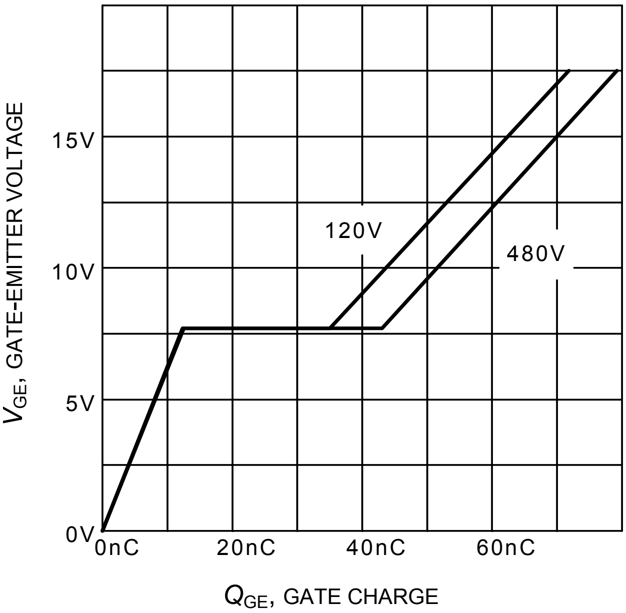


Figure 17. Typical gate charge
(I_C=10 A)

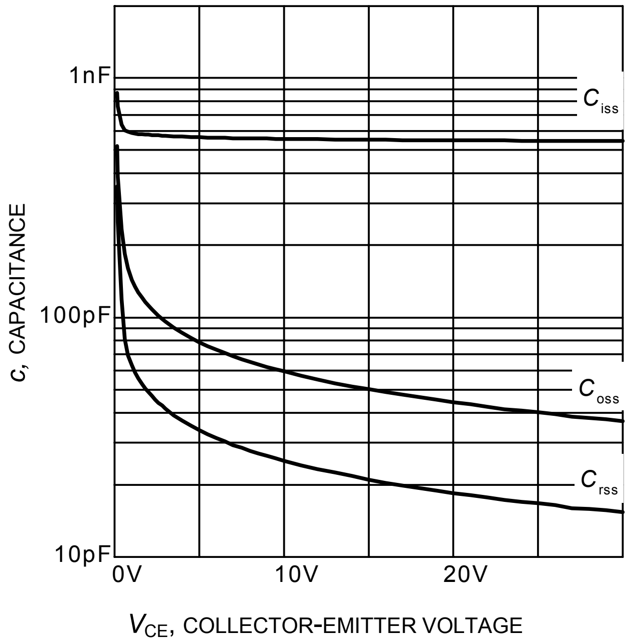


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

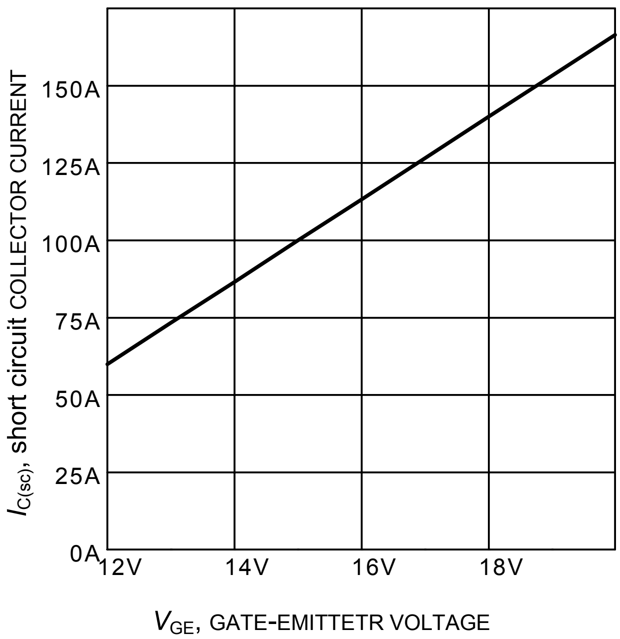


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq$ 400V, $T_j \leq$ 150°C)

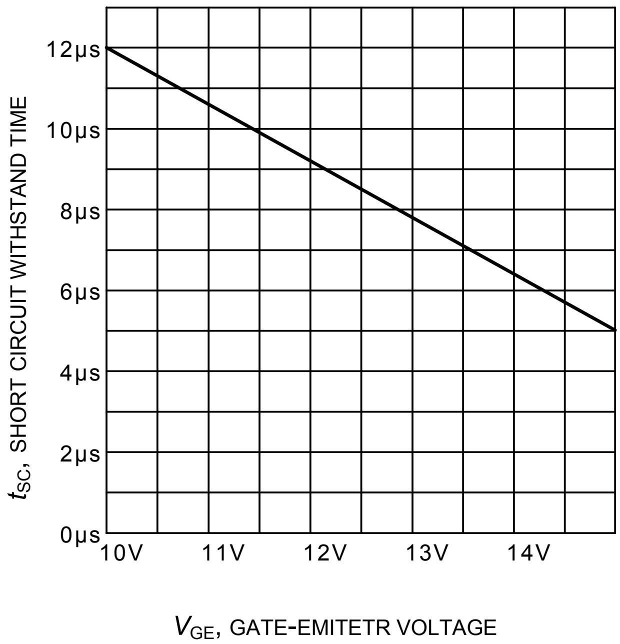


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=600V, start at T_J=25°C, T_{Jmax}<150°C)

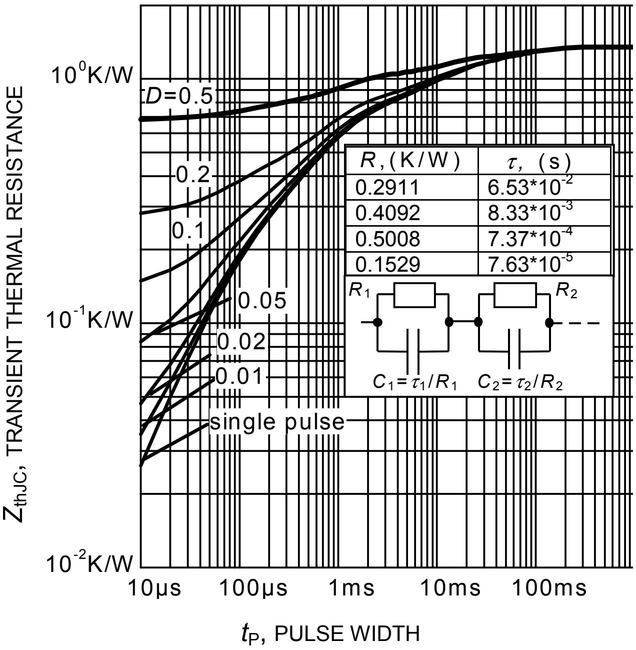


Figure 21. IGBT transient thermal resistance
($D = t_p / T$)

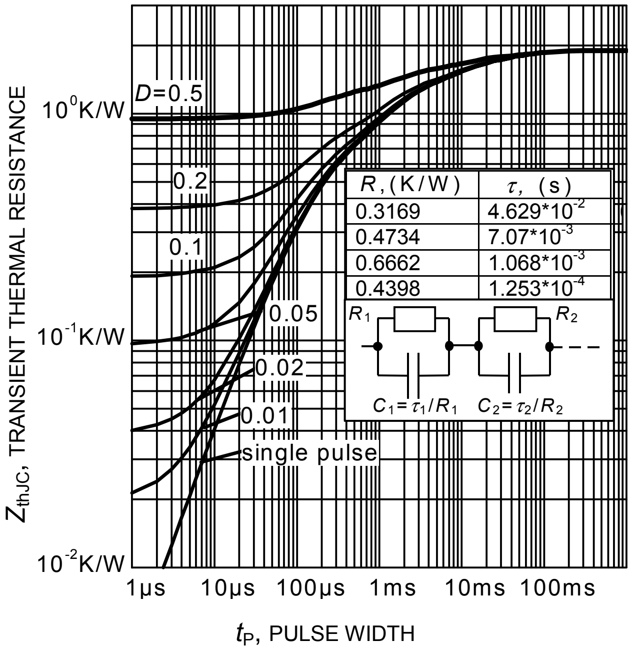


Figure 22. Diode transient thermal impedance as a function of pulse width
($D=t_P/T$)

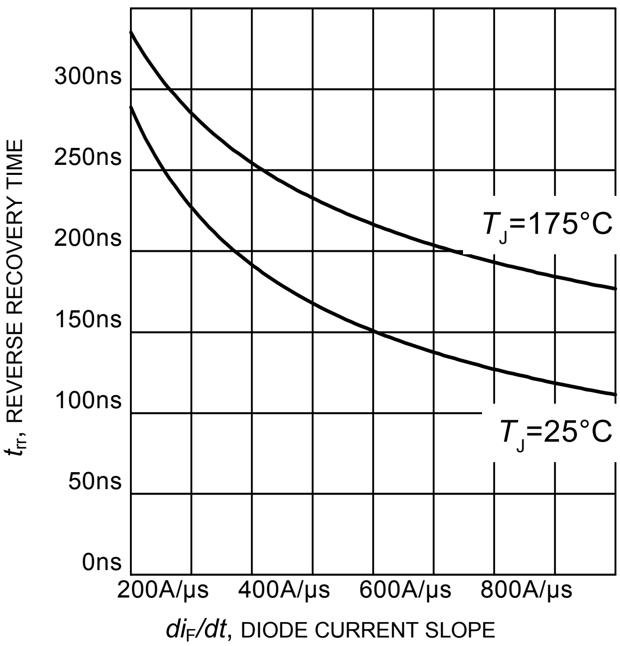


Figure 23. Typical reverse recovery time as a function of diode current slope
(V_R=400V, I_F=10A,
Dynamic test circuit in Figure E)

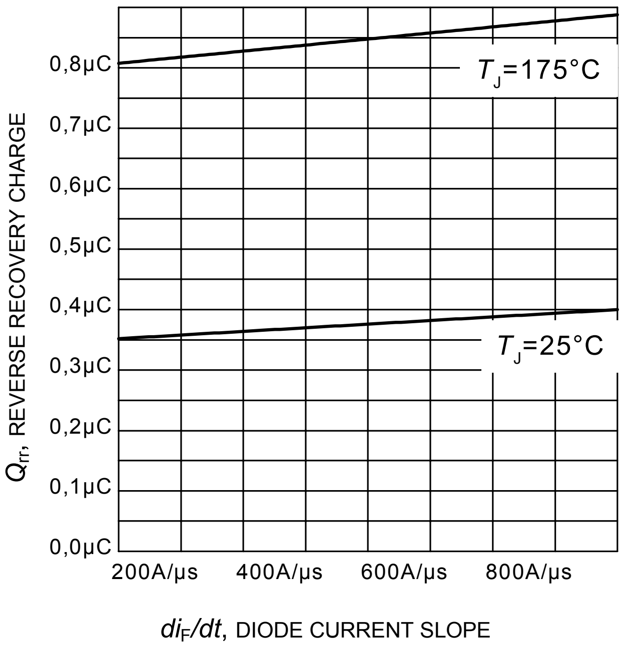


Figure 24. Typical reverse recovery charge as a function of diode current slope
(V_R = 400V, I_F = 10A,
Dynamic test circuit in Figure E)

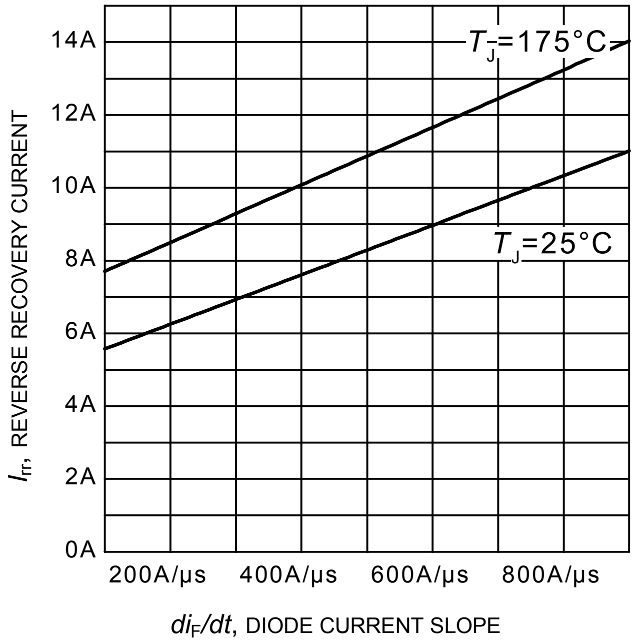


Figure 25. Typical reverse recovery current as a function of diode current slope
(V_R = 400V, I_F = 10A,
Dynamic test circuit in Figure E)

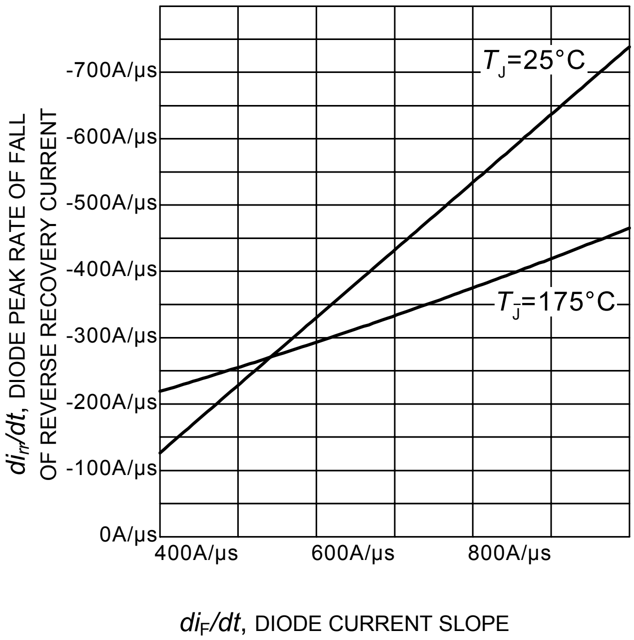


Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=400V, I_F=10A,
Dynamic test circuit in Figure E)

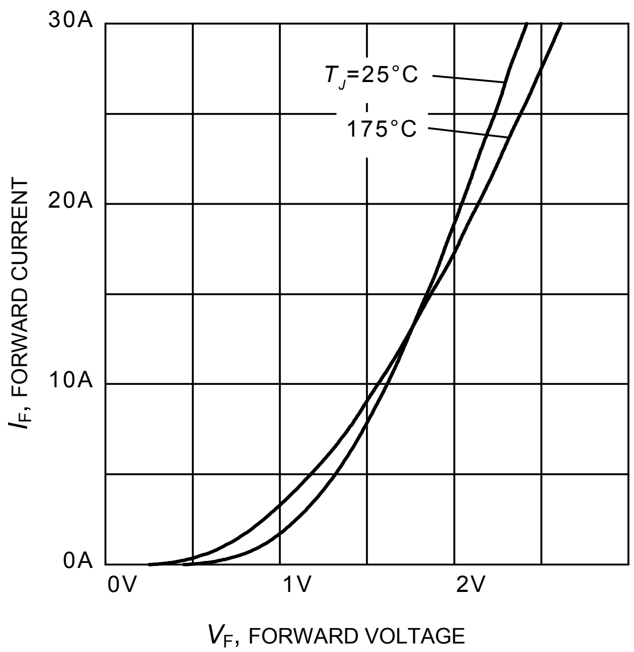


Figure 27. Typical diode forward current as a function of forward voltage

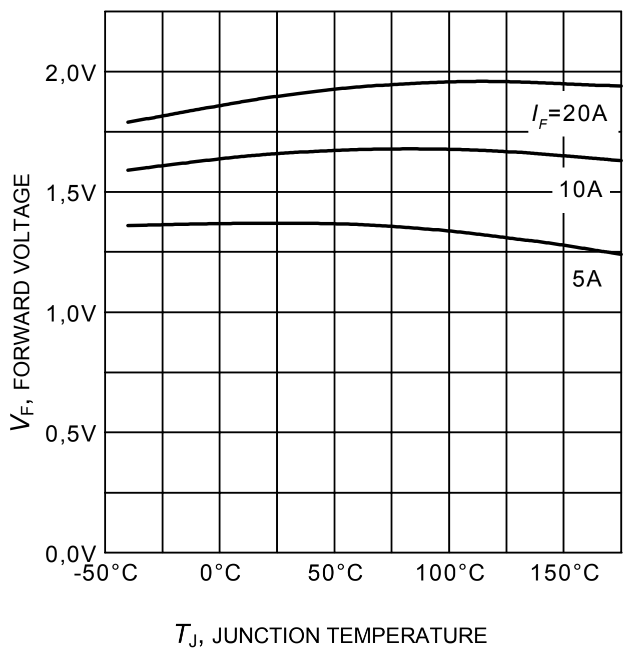


Figure 28. Typical diode forward voltage as a function of junction temperature

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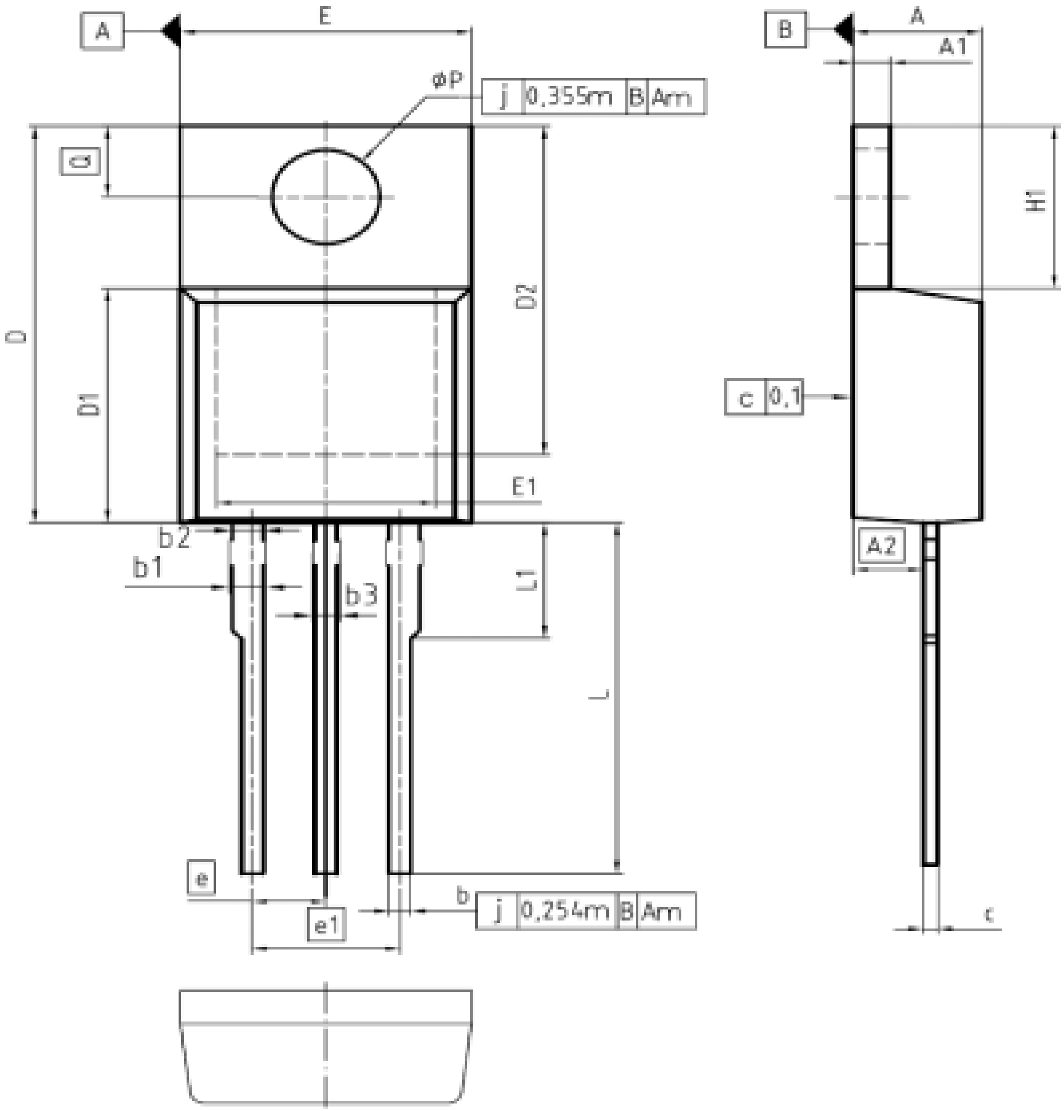

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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SCALE 0 2.5 5mm

EUROPEAN PROJECTION

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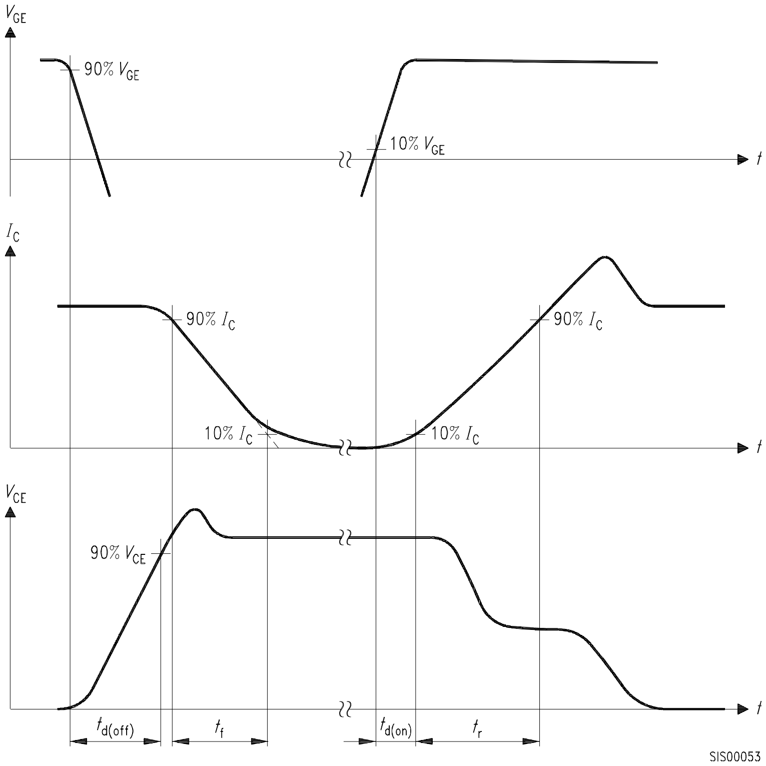

Figure A. Definition of switching times

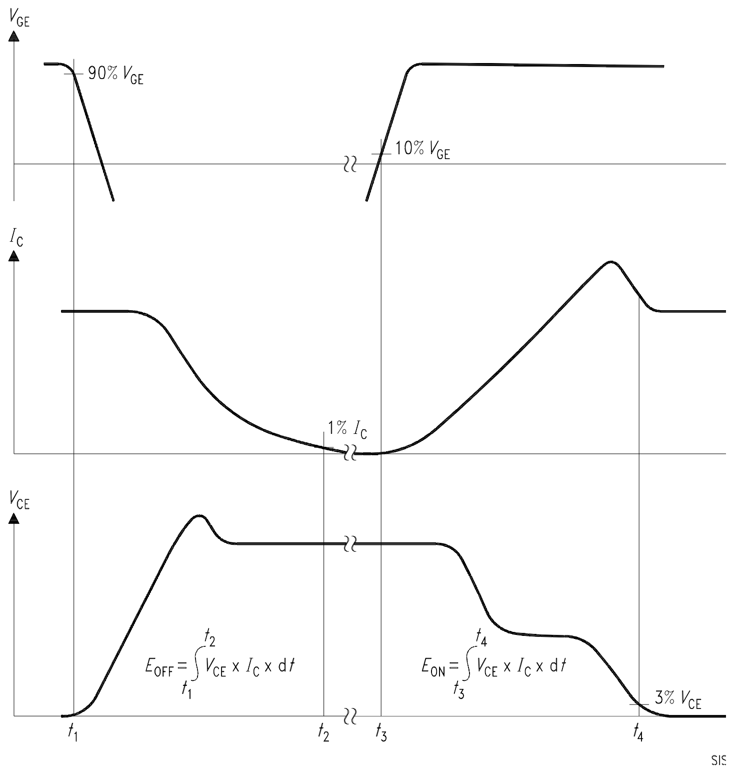

Figure B. Definition of switching losses

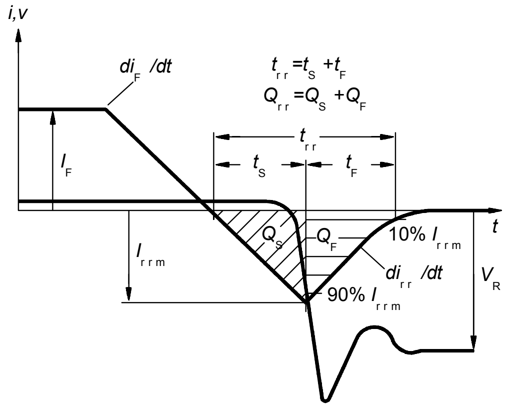

Figure C. Definition of diodes switching characteristics

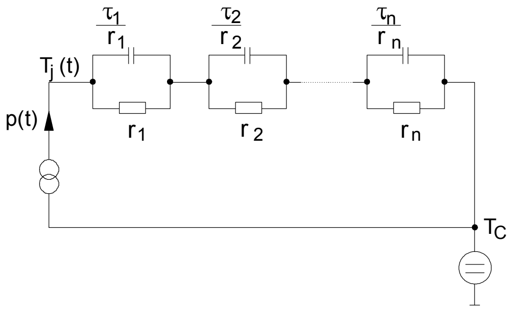

Figure D. Thermal equivalent circuit

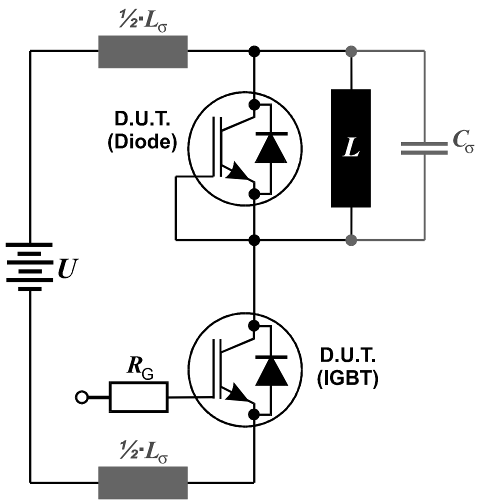

Figure E. Dynamic test circuit
Leakage inductance L_{σ} =60nH and Stray capacity C_{σ} =40pF.

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